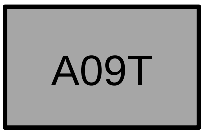
AO3400A

N-Channel Enhanceme Mode Field Effect Transistor

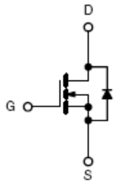
V_{DSS}	30	V
I_D	5.8	A
$R_{DS(ON)}$	21	mΩ

FEATURES

High density cell design for low $R_{DS(ON)}$
Voltage controlled small signal switch
Rugged and reliable
High saturation current capability



SOT23-3L top view



Schematic Diagram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	5.8	A
Drain Current-Pulsed (note 1)	I_{DM}	30	A
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

Electrical characteristics (T_J =25℃ unless otherwise noted)

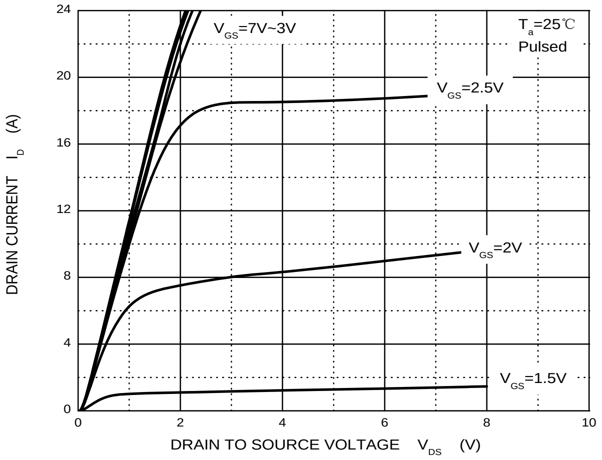
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =24V,V_{GS} = 0V			1	μA
Gate-source leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
On characteristics						
Drain-source on-resistance (note 3)	$R_{DS(on)}$	V_{GS} =10V, I_D =5.8A		21	28	mΩ
		V_{GS} =4.5V, I_D =5A			38	mΩ
		V_{GS} =2.5V,I_D=4A			52	mΩ
Forward tranconductance	g_{FS}	V_{DS} =5V, I_D =5A	8			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.7		1.4	V
Dynamic Characteristics (note 4,5)						
Input capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V,f =1MHz			1050	pF
Output capacitance	C_{oss}			99		pF
Reverse transfer capacitance	C_{rss}			77		pF
Gate resistance	R_g	V_{DS} =0V,V_{GS} =0V,f =1MHz			3.6	Ω
Switching Characteristics (note 4,5)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V,V_{DS}=15V, R_L=2.7Ω,R_{GEN}=3Ω			5	ns
Turn-on rise time	t_r				7	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall time	t_f				6	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 3)	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note :

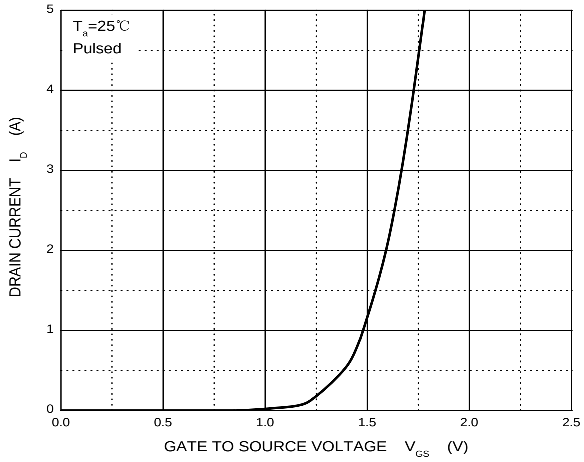
1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

RATING AND CHARACTERISTIC CURVES

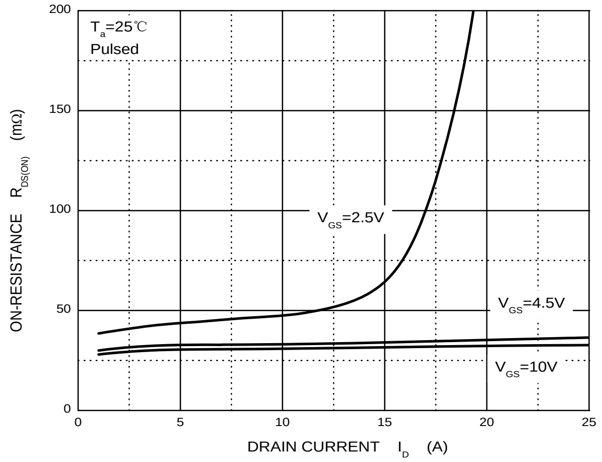
Output Characteristics



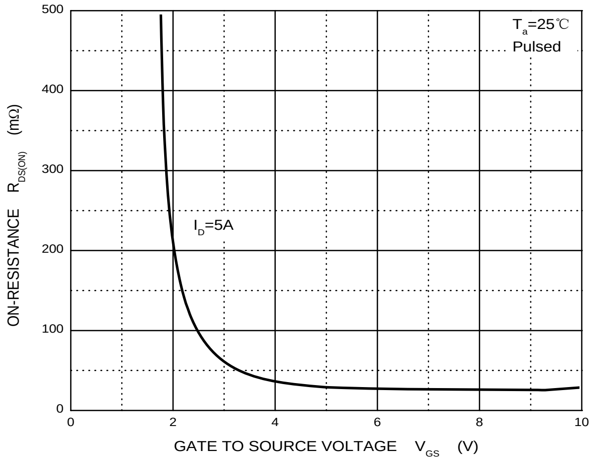
Transfer Characteristics



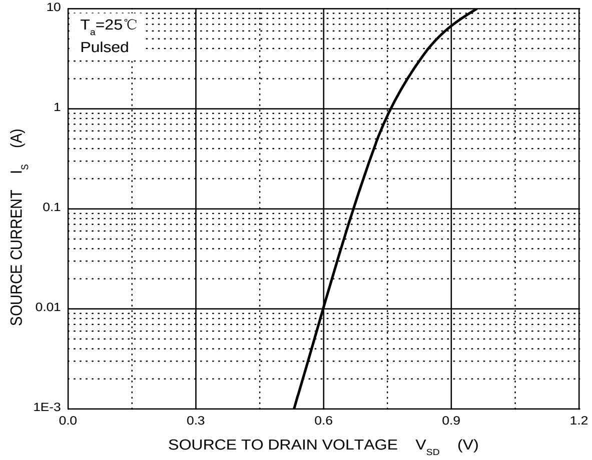
$R_{DS(ON)}$ —— I_D



$R_{DS(ON)}$ —— V_{GS}



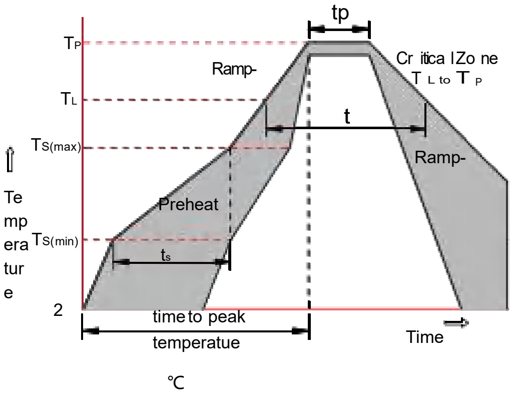
I_S —— V_{SD}



Soldering parameters

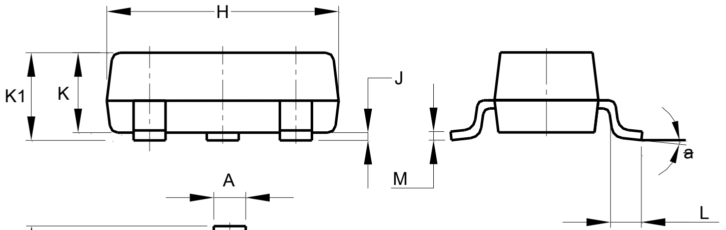
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

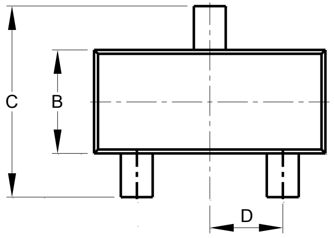
FIG5: Reflow condition

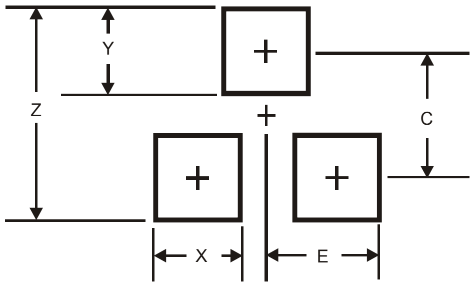


Package Dimensions & Suggested Pad Layout

SOT23-3L





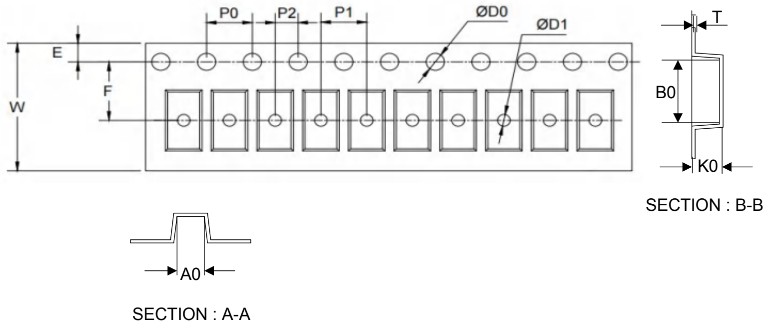


SOT23-3L		
Dim	**Min**	**Max**
A	0.30	0.50
B	1.50	1.70
C	2.65	2.95
D	0.90	1.00
H	2.82	3.02
J		0.10
K	1.05	1.15
K1	1.05	1.25
L	0.30	0.60
M	0.10	0.20
a	0°	8°
All Dimensions in mm		

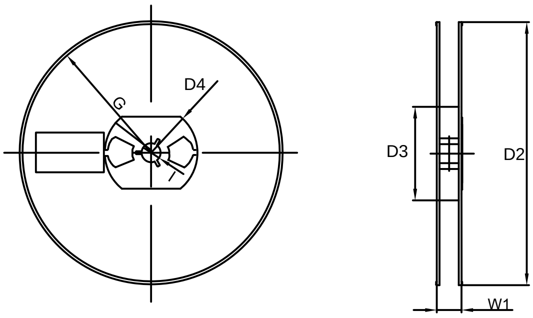
Dimensions	SOT23-3L
Z	3.3
X	0.9
Y	1.0
C	2.3
E	1.40

Tape & rell specification

Tape



7” Reel



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.05±0.20
E	1.55±0.20
F	3.60±0.20
W	8.00±0.20
A0	3.80±0.20
B0	3.50±0.20
K0	1.55±0.20
T	0.25±0.15
D2	178.0±5.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

Quantity: 3000PCS